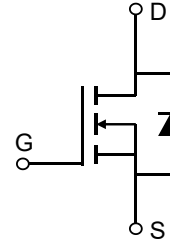


Description

Features

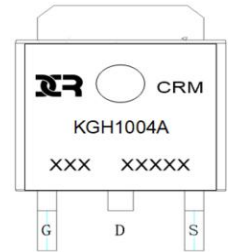
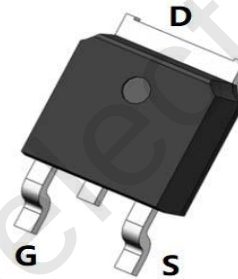
- 100V, 110A
 $R_{DS(ON)}$ Typ = 4.9mΩ @ $V_{GS} = 10V$
- Advanced Split Gate Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS TESTED!
- 100% ΔV_{ds} TESTED!



Schematic Diagram

Application

- Load Switch
- PWM Application
- Power Management



Marking and Pin Assignment

Package Marking and Ordering Information

Device	Marking	Package	Outline	Reel Size	Reel (pcs)	Per Carton (pcs)
CRMKGH1004A	CRMKGH1004A	TO-252-3L	TAPING	13"	2500	25000

Absolute Maximum Ratings (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Units	
V _{DS}	Drain-to-Source Voltage	100	V	
V _{GS}	Gate-to-Source Voltage	±20	V	
I _D	Continuous Drain Current	T _C = 25°C	110	A
		T _C = 100°C	66	A
I _{DM}	Pulsed Drain Current ⁽¹⁾	440	A	
E _{AS}	Single Pulsed Avalanche Energy ⁽²⁾	240	mJ	
P _D	Power Dissipation	T _C = 25°C	130	W
R _{θJC}	Thermal Resistance, Junction to Case	0.96	°C/W	
T _J , T _{STG}	Junction & Storage Temperature Range	-55 to 150	°C	

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
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Off Characteristics

$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	100	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 100\text{V}, V_{GS} = 0\text{V}$	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$	-	-	± 100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	2.4	3	3.6	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance ⁽³⁾	$V_{GS} = 10\text{V}, I_D = 20\text{A}$	-	4.9	6.3	mΩ

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}, V_{DS} = 50\text{V},$ $f = 1\text{MHz}$	-	2800	-	pF
C_{oss}	Output Capacitance		-	1295	-	pF
C_{rss}	Reverse Transfer Capacitance		-	20	-	pF
Q_g	Total Gate Charge	$V_{GS} = 0 \text{ to } 10\text{V}$ $V_{DS} = 50\text{V}, I_D = 20\text{A}$	-	45	-	nC
Q_{gs}	Gate Source Charge		-	7.5	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	12	-	nC

Switching Characteristics

$t_{d(on)}$	Turn-On DelayTime	$V_{GS} = 10\text{V}, V_{DD} = 50\text{V}$ $I_D = 20\text{A}, R_{GEN} = 2.5\Omega$	-	13	-	ns
t_r	Turn-On Rise Time		-	20	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	50	-	ns
t_f	Turn-Off Fall Time		-	40	-	ns

Drain-Source Diode Characteristics and Max Ratings

I_S	Maximum Continuous Drain to Source Diode Forward Current	$V_{GS} = 0\text{V}, I_S = 20\text{A}$	-	-	110	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	440	A
V_{SD}	Drain to Source Diode Forward Voltage		-	-	1.2	V
t_{rr}	Body Diode Reverse Recovery Time		-	54.7	-	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	76	-	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2. E_{AS} condition: Starting $T_J = 25^\circ\text{C}$, $V_{DD} = 50\text{V}$, $V_G = 10\text{V}$, $R_G = 25\Omega$, $L = 0.5\text{mH}$, $I_{AS} = 31\text{A}$
3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.

Test Circuit

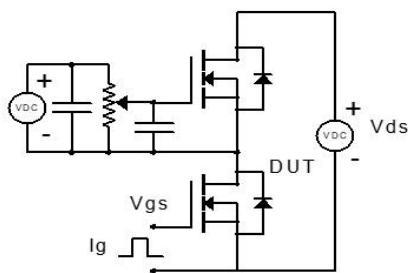


Figure 1: Gate Charge Test Circuit & Waveform

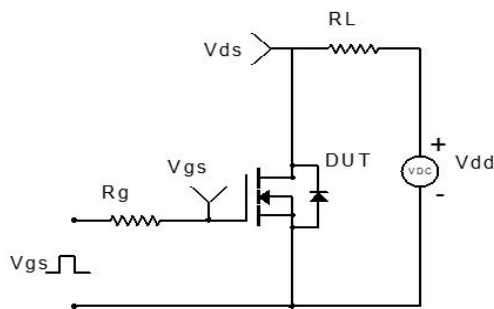


Figure 2: Resistive Switching Test Circuit & Waveform

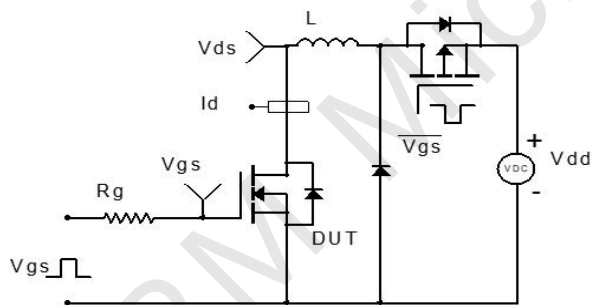


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

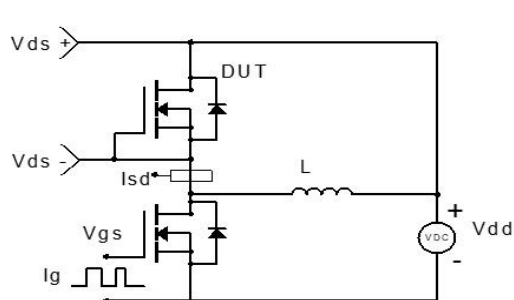
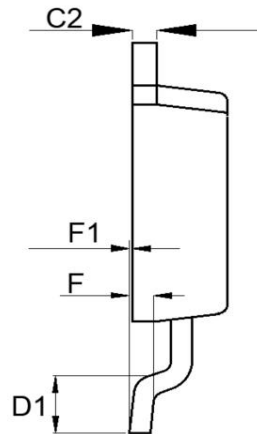
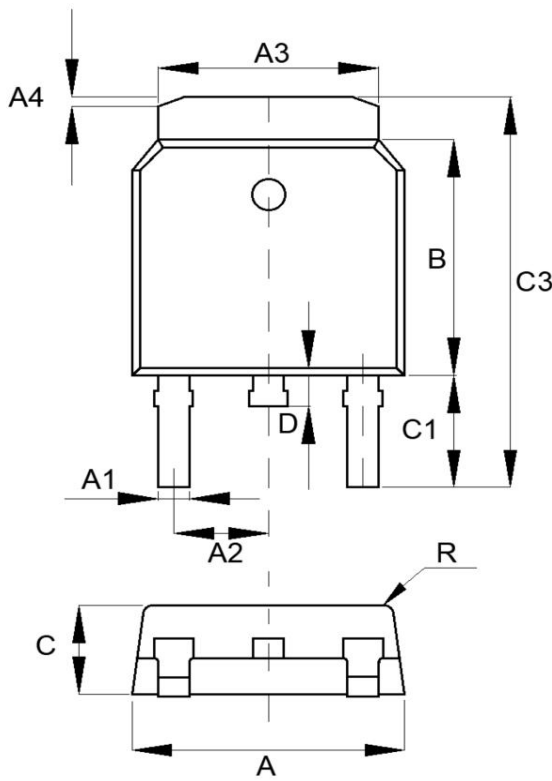


Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(TO-252-3L)



SYMBOL	MIN	NOM	MAX
A	6.550	6.600	6.650
A1	0.640	0.690	0.740
A2	—	2.286	—
A3	5.234	5.334	5.434
A4	0.070	0.270	0.470
B	6.050	6.100	6.150
C	2.250	2.300	2.350
C1	2.650	2.780	2.950
C2	0.504	0.508	0.510
C3	9.750	9.850	10.00
D	0.700	0.800	0.900
D1	1.400	1.500	1.600
F	—	0.508	—
F1	0	0.050	0.100
R	—	0.250	—

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Contact information

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